MGBR20L150C DIODE

DUAL MOS GATED BARRIER RECTIFIER

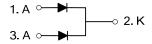
■ DESCRIPTION

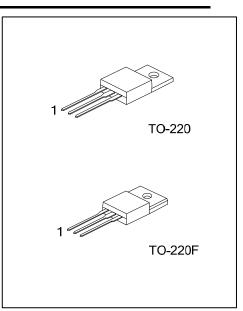
The UTC MGBR20L150C is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

- * Low forward voltage drop
- * High switching speed

■ SYMBOL

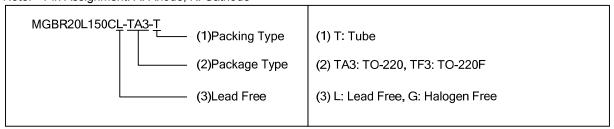




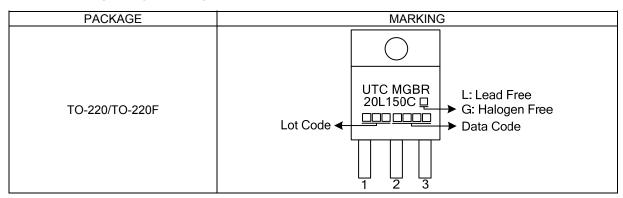
■ ORDERING INFORMATION

Ordering Number		Doolsogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR20L150CL-TA3-T	MGBR20L150CG-TA3-T	TO-220	Α	K	Α	Tube	
MGBR20L150CL-TF3-T	MGBR20L150CG-TF3-T	TO-220F	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode, K: Cathode



■ MARKING INFORMATION



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MGBR20L150C DIODE

■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V_{RM}	150	V
Working Peak Reverse Voltage		V_{RWM}	150	V
Peak Repetitive Reverse Voltage		V_{RRM}	150	V
Average Rectified Output Current Per Device	Per Leg	l _o	10	Α
	Total		20	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I _{FSM}	150	Α
Operating Junction Temperature		T_J	-65~+150	°C
Storage Temperature		T_{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient		θ_{JA}	62.5	°C/W	
Junction to Case	TO-220	0	2	°0.041	
	TO-220F	θις	3.31	°C/W	

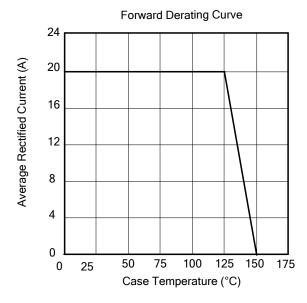
■ ELECTRICAL CHARACTERISTICS (PER LEG) (T_A =25°C unless otherwise specified.)

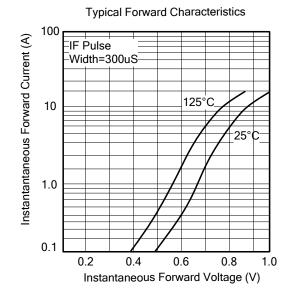
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.50mA	150			V
Forward Voltage Drop	I V _{EM}	I _F =10A, T _J =25°C			0.90	V
		I _F =10A, T _J =125°C			0.85	V
Lastras Ormant (Nata 4)	PМ	V _R =150V, T _J =25°C			50	μA
Leakage Current (Note 1)		V _R =150V, T _J =125°C			20	mA

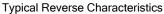
Notes: 1. Short duration pulse test used to minimize self-heating effect.

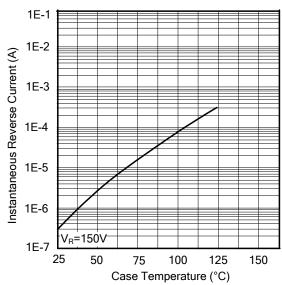
^{2.} Thermal resistance junction to case mounted on heatsink.

■ TYPICAL CHARACTERISTICS









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